

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S259	10017	(438/151,197,201,257,258,261,263).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/23 16:03
S260	8678	(257/314,315,321,E21.422,E21.68,E21.687,E21.688,E29.129,E29.3).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/23 16:04
S261	247	(257/E21.683).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/23 16:05
S262	16694	S259 or S260 or S261	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:05
S263	13	438/FOR.431.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:06

S264	427074	(pattern\$4 or etch\$4 or remov\$4) near8 (polysi or poly-si or polysilicon or poly-silicon or control or floating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:07
S265	739904	(cell or memory or core) same (peripheral or periphery or logic or ((high or low) near voltage) or HV or LV or NMOS or PMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:09
S266	418150	(dielectric or insulator or insulating or insulated) same (oxide or nitride or oxide\$nitride or oxide \$nitride\$oxide or ONO or O-N-O or SiO or SiN or "SiO.sub.2" or "Si.sub.3N.sub.4")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:11
S267	18515	S264 and S265 and S266	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:11
S268	7174	S267 and (control near gate) and (floating near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:12
S269	6898	S268 and (source/drain or source or drain or S/D)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:12

S270	4784	S269 and (flash near memory)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:12
S271	2171	S270 and ((@ad<"20011228") or (@rlad<"20011228"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:13
S272	985	S271 and cell and peripheral	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:13
S273	38829	Hynix.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:23
S274	916172	Kim.in. or Jung.in. or Cho.in. or Lee.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:24
S275	17	S272 and S273	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:24

S276	968	S272 not S275	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:26
S277	91285	(cell with peripheral)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:27
S278	624	S276 and S277	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:27
S279	26548	(oxide or nitride or oxide\$nitride or oxide\$nitride \$oxide or ONO or O-N-O or SiO or SiN or "SiO. sub.2" or "Si.sub.3N.sub.4") with ((control or floating) near4 gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:29
S280	570	S278 and S279	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/23 16:29
S281	14	("5668034" "5760438" "5780889" "5812451" "5841161" "5861347" "5904518").PN. OR ("6667511").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/23 17:09

S282	70	("4173766" "5168334" "5349221" "5712208" "5768192" "5825686" "5889303" "5966603" "6001709" "6030871" "6093607").PN. OR ("6445030").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/23 17:19
S283	19	("20020032891" "20020060929" "20030067807" "20030067809" "20030128591" "4353083" "4635229" "5493141" "5739569" "6005809" "6327187" "6418040" "6426897" "6436768" "6445030" "6448137" "6465306").PN. OR ("6834013").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/23 17:31
S284	36	("4282540" "4608585" "4794333" "4794562" "4962481").PN. OR ("5066992").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/23 18:19
S285	2	("6787840").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/24 09:46
S286	7936	(pattern\$4 or remov\$4 or etch\$4) same (oxide or nitride or ONO or oxide/nitride or oxide/nitride/oxide) same control same floating	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:55
S287	259226	(cell and peripheral)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:55

S288	2180	S286 and S287	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:56
S289	1026	S288 and ((@ad<"20010626") or (@lad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/24 09:56
S290	532	S289 and (flash near memory)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/24 09:57
S291	91775	(oxide or nitride or ONO or oxide/nitride or oxide/ nitride/oxide) near8 (gate near (oxide or dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:58
S292	409	S290 and S291	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:58
S293	1537	(ONO or oxide/nitride or oxide/nitride/oxide) near8 (gate near (oxide or dielectric))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:58

S294	38	S290 and S293	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 09:59
S295	11	("5449629" "5674762" "5879990" "5963808" "5976934" "6023085" "6087211").PN. OR ("6274430").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/24 10:09
S296	38	("4823175" "5290725" "5300802" "5321287" "5508957" "5574685" "5668034" "5907171"). PN. OR ("6023085").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/02/24 10:13
S297	287	S293 with (control near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/02/24 10:33
S298	93	S297 and ((@ad<"20010626") or (@lad<"20010626"))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/24 10:33
S299	91	S298 and (cell or memory or core)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/24 10:34
S300	2	("6667511").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/02/27 16:47

2/27/2009 11:20:20 PM

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